



BOTTOM SIDE (MCC-I2 = 6840 x 5140 μ m²)

<i>Pin Name</i>	<i>X</i>	<i>Y</i>	<i>WB Type</i>
DTIAN<8>	720 μ m	143 μ m	AMS
DTIAP<8>	870 μ m	143 μ m	AMS
DTIAN<9>	1,270 μ m	143 μ m	AMS
DTIAP<9>	1,420 μ m	143 μ m	AMS
DTIAN<10>	1,820 μ m	143 μ m	AMS
DTIAP<10>	1,970 μ m	143 μ m	AMS
DTIAN<11>	2,370 μ m	143 μ m	AMS
DTIAP<11>	2,520 μ m	143 μ m	AMS
DTIAN<12>	2,920 μ m	143 μ m	AMS
DTIAP<12>	3,070 μ m	143 μ m	AMS
DTIAN<13>	3,470 μ m	143 μ m	AMS
DTIAP<13>	3,620 μ m	143 μ m	AMS
GND7	3,920 μ m	143 μ m	FH/AMS
VDD7	4,220 μ m	143 μ m	FH/AMS
DTIAN<14>	4,520 μ m	143 μ m	AMS
DTIAP<14>	4,670 μ m	143 μ m	AMS
DTIAN<15>	5,070 μ m	143 μ m	AMS
DTIAP<15>	5,220 μ m	143 μ m	AMS
LDA	5,520 μ m	143 μ m	AMS
CCKA	5,820 μ m	143 μ m	AMS
TSTIN	6,120 μ m	143 μ m	TEST

Positions are measured from the bottom left corner of the chip_edge

TOP SIDE (MCC-I2 = 6840 x 5140 μ m²)

<i>Pin Name</i>	<i>X</i>	<i>Y</i>	<i>WB Type</i>
DTIp<8>	720 μ m	4,997 μ m	FH
DTIn<8>	870 μ m	4,997 μ m	FH
DTIp<7>	1,020 μ m	4,997 μ m	FH/AMS
DTIn<7>	1,170 μ m	4,997 μ m	FH/AMS
DTIp<9>	1,320 μ m	4,997 μ m	FH
DTIn<9>	1,470 μ m	4,997 μ m	FH
DTIp<6>	1,620 μ m	4,997 μ m	FH/AMS
DTIn<6>	1,770 μ m	4,997 μ m	FH/AMS
DTIp<10>	1,920 μ m	4,997 μ m	FH
DTIn<10>	2,070 μ m	4,997 μ m	FH
DTIp<5>	2,220 μ m	4,997 μ m	FH/AMS
DTIn<5>	2,370 μ m	4,997 μ m	FH/AMS
DTIp<11>	2,520 μ m	4,997 μ m	FH
DTIn<11>	2,670 μ m	4,997 μ m	FH
DTIp<4>	2,820 μ m	4,997 μ m	FH/AMS
DTIn<4>	2,970 μ m	4,997 μ m	FH/AMS
DTIp<12>	3,120 μ m	4,997 μ m	FH
DTIn<12>	3,270 μ m	4,997 μ m	FH
DTIp<3>	3,420 μ m	4,997 μ m	FH/AMS
DTIn<3>	3,570 μ m	4,997 μ m	FH/AMS
DTIp<13>	3,720 μ m	4,997 μ m	FH
DTIn<13>	3,870 μ m	4,997 μ m	FH
DTIp<2>	4,020 μ m	4,997 μ m	FH/AMS
DTIn<2>	4,170 μ m	4,997 μ m	FH/AMS
VDD3	4,320 μ m	4,997 μ m	FH/AMS
GND3	4,470 μ m	4,997 μ m	FH/AMS
DTIp<14>	4,620 μ m	4,997 μ m	FH
DTIn<14>	4,770 μ m	4,997 μ m	FH
DTIp<1>	4,920 μ m	4,997 μ m	FH/AMS
DTIn<1>	5,070 μ m	4,997 μ m	FH/AMS
DTIp<15>	5,220 μ m	4,997 μ m	FH
DTIn<15>	5,370 μ m	4,997 μ m	FH
DTIp<0>	5,520 μ m	4,997 μ m	FH/AMS
DTIn<0>	5,670 μ m	4,997 μ m	FH/AMS
DAO	5,820 μ m	4,997 μ m	FH/AMS
RSOb	5,970 μ m	4,997 μ m	FH/AMS
TSTEN	6,120 μ m	4,997 μ m	TEST

Positions are measured from the bottom left corner of the chip_edge

LEFT SIDE (MCC-I2 = 6840 x 5140 μ m²)

<i>Pin Name</i>	<i>X</i>	<i>Y</i>	<i>WB Type</i>
VDD6	143 μ m	1,670 μ m	FH/AMS
GND6	143 μ m	1,820 μ m	FH/AMS
AMSDSM	143 μ m	1,970 μ m	FH
SYNCp	143 μ m	2,120 μ m	FH/AMS
SYNCn	143 μ m	2,270 μ m	FH/AMS
XCKINp	143 μ m	2,420 μ m	FH/AMS
XCKINn	143 μ m	2,570 μ m	FH/AMS
XCKp	143 μ m	2,720 μ m	FH/AMS
XCKn	143 μ m	2,870 μ m	FH/AMS
VDD5	143 μ m	3,020 μ m	FH/AMS
GND5	143 μ m	3,170 μ m	FH/AMS
STROp	143 μ m	3,320 μ m	FH/AMS
STROn	143 μ m	3,470 μ m	FH/AMS
LV1p	143 μ m	3,620 μ m	FH/AMS
LV1n	143 μ m	3,770 μ m	FH/AMS
VDD4	143 μ m	3,920 μ m	FH/AMS
GND4	143 μ m	4,070 μ m	FH/AMS

Positions are measured from the bottom left corner of the chip_edge

RIGHT SIDE (MCC-I2 = 6840 x 5140 μ m²)

<i>Pin Name</i>	<i>X</i>	<i>Y</i>	<i>WB Type</i>
GND0	6,697 μ m	1,520 μ m	FH
VDD0	6,697 μ m	1,670 μ m	FH
LD	6,697 μ m	1,820 μ m	FH
CCK	6,697 μ m	1,970 μ m	FH
RSIb	6,697 μ m	2,120 μ m	FH/AMS
DT02n	6,697 μ m	2,270 μ m	FH
DT02p	6,697 μ m	2,420 μ m	FH
DT0n	6,697 μ m	2,570 μ m	FH/AMS
DT0p	6,697 μ m	2,720 μ m	FH/AMS
GND1	6,697 μ m	2,870 μ m	FH/AMS
VDD1	6,697 μ m	3,020 μ m	FH/AMS
TSTOUT	6,697 μ m	3,170 μ m	TEST
DCIn	6,697 μ m	3,320 μ m	FH/AMS
DCIp	6,697 μ m	3,470 μ m	FH/AMS
CKn	6,697 μ m	3,620 μ m	FH/AMS
CKp	6,697 μ m	3,770 μ m	FH/AMS
GND2	6,697 μ m	3,920 μ m	FH
VDD2	6,697 μ m	4,070 μ m	FH

Positions are measured from the bottom left corner of the chip_edge